INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

Docket Number (Optional)	Application Number
BUR920020068US1	10/539,247
Applicant(s)	
Anne Gattiker et al.	
Filing Date	**Group Art Unit**
June 16, 2005	2820

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

U.S. PATENT APPLICATION PUBLICATIONS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation YES	Translation NO

OTHER DOCUMENTS *(Including Author, Title, Date, Pertinent Pages, Etc.)*

VN		Ali Keshavarzi et al., "Intrinsic Leakage in Low Power Deep Submicron CMOS ICs", International Test Conference 1997 (IEEE Cat. No. 97CH36126), pp. 146-155.

EXAMINER	/Vinh Nguyen/	DATE CONSIDERED	01/17/2007

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

PAGE 3/13 * RCVD AT 6/9/2006 11:32:34 AM [Eastern Daylight Time] * SVR:USPTO-EFXRF-5/16 * DNIS:2738300 * CSID:845 892 6363 * DURATION (mm-ss):05-02